

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
12V	16mΩ @ V <sub>GS</sub> = 4.5V	8.0A
	25mΩ @ V <sub>GS</sub> = 2.5V	6.5A

## Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

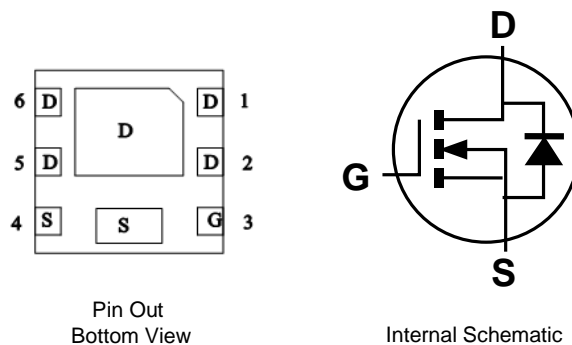
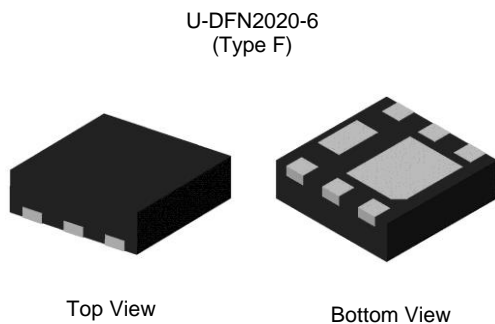
- Battery Management Application
- Power Management Functions
- DC-DC Converters

## Features

- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. “Green” Device (Note 3)**
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

## Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>(e4)</sup>
- Weight: 0.0065 grams (Approximate)



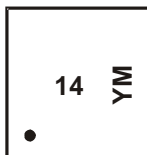
## Ordering Information (Note 4)

Part Number	Reel Size (inches)	Case	Quantity per Reel
DMN1014UFDF-7	7	U-DFN2020-6 (Type F)	3,000
DMN1014UFDF-13	13	U-DFN2020-6 (Type F)	10,000

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

Site 1



14 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: H = 2020)  
 M = Month (ex: 9 = September)

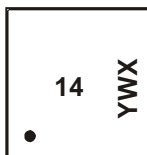
Date Code Key

Year	2017	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	E	...	H	I	J	K	L	M	N	O	P	R

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



14 = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 0 = 2020)  
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2017	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	7	...	0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	12	V
Gate-Source Voltage	V <sub>GSS</sub>	±8	V
Continuous Drain Current, V <sub>GS</sub> = 4.5V (Note 6)	Steady State	T <sub>A</sub> = +25°C	8
		T <sub>A</sub> = +70°C	6
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	40	A
Continuous Source-Drain Diode Current (Note 6)	I <sub>S</sub>	2.1	A
Pulsed Source-Drain Diode Current (380µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	40	A
Avalanche Current, L = 0.1mH (Note 7)	I <sub>AS</sub>	10.8	A
Avalanche Energy, L = 0.1mH (Note 7)	E <sub>AS</sub>	5.8	mJ

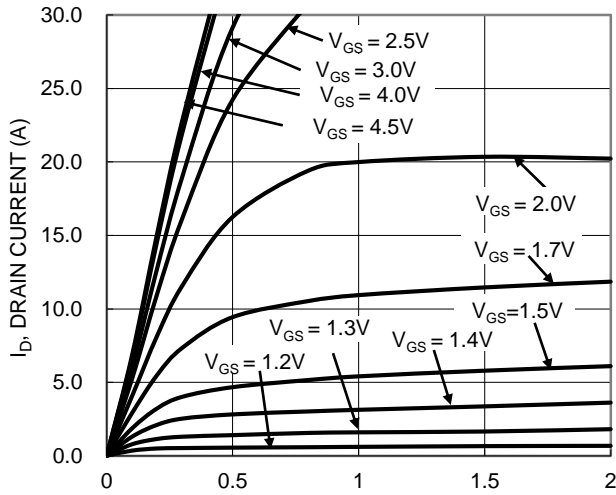
**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	T <sub>A</sub> = +25°C	0.7
		T <sub>A</sub> = +70°C	0.4
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	177	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	T <sub>A</sub> = +25°C	1.7
		T <sub>A</sub> = +70°C	1.0
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	76	°C/W
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	15.5	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

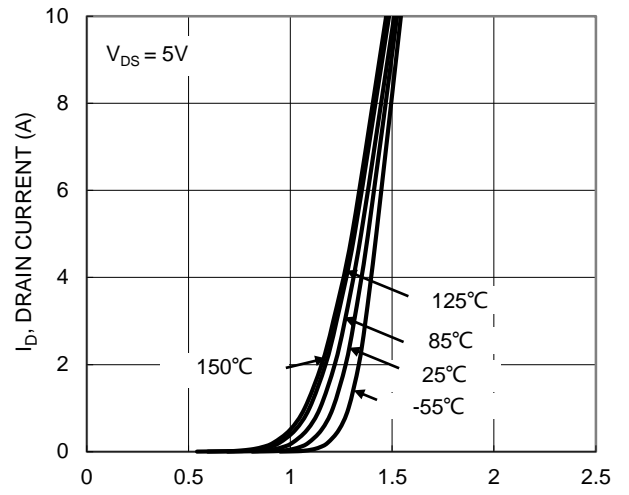
**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	12	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 9.6V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.3	—	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	12	16	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2A
			16	25		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 2A
Diode Forward Voltage	V <sub>SD</sub>	—	0.72	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 2A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	515	—	pF	V <sub>DS</sub> = 6V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	155	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	121	—		
Gate Resistance	R <sub>g</sub>	—	2.4	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	6.4	—	nC	V <sub>DS</sub> = 6V, I <sub>D</sub> = 2A
Gate-Source Charge	Q <sub>gs</sub>	—	0.3	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	1.9	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.0	—	ns	V <sub>DS</sub> = 6V, V <sub>GS</sub> = 4.5V, R <sub>g</sub> = 2Ω, I <sub>D</sub> = 2A
Turn-On Rise Time	t <sub>r</sub>	—	3.6	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	12.4	—		
Turn-Off Fall Time	t <sub>f</sub>	—	4.4	—		
Reverse Recovery Time	t <sub>RR</sub>	—	9.5	—	ns	I <sub>F</sub> = 2A, di/dt = 200A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	1.7	—	nC	I <sub>F</sub> = 2A, di/dt = 200A/µs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)  
Figure 1. Typical Output Characteristic



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V)  
Figure 2. Typical Transfer Characteristic

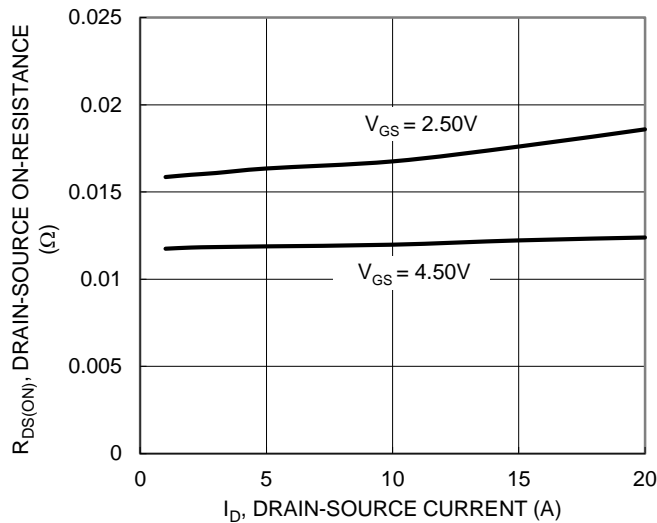
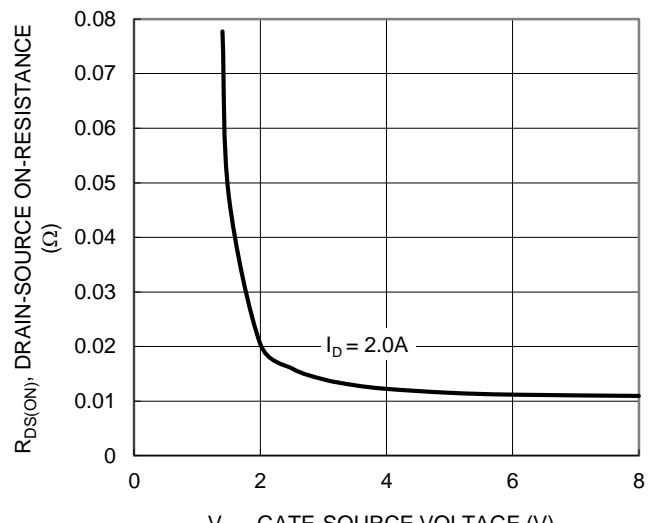


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V)  
Figure 4. Typical Transfer Characteristic

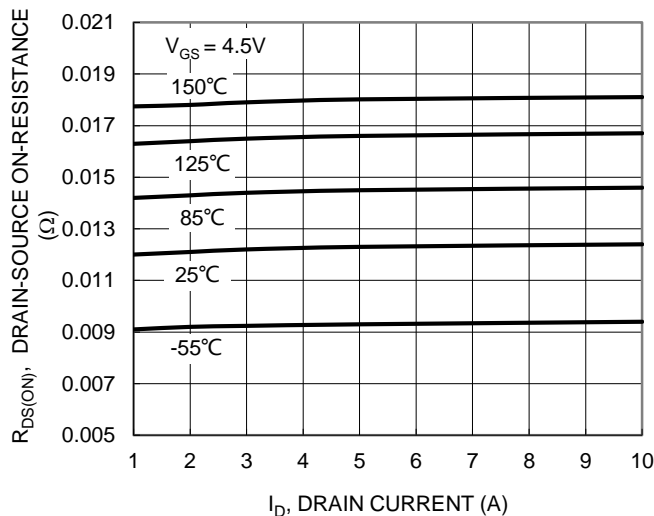


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

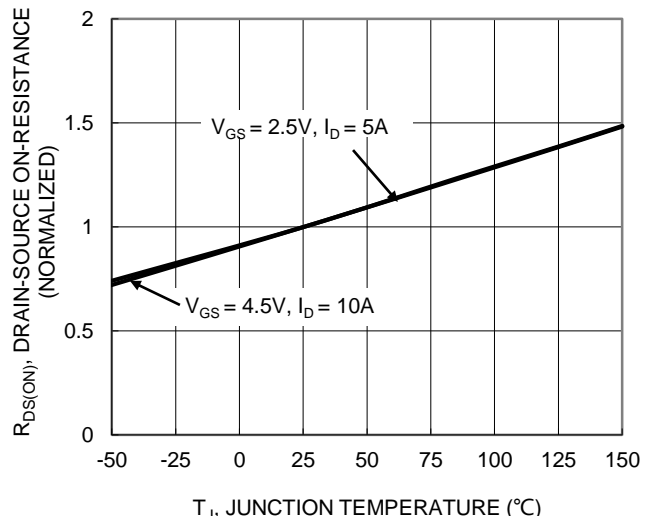


Figure 6. On-Resistance Variation with Junction Temperature

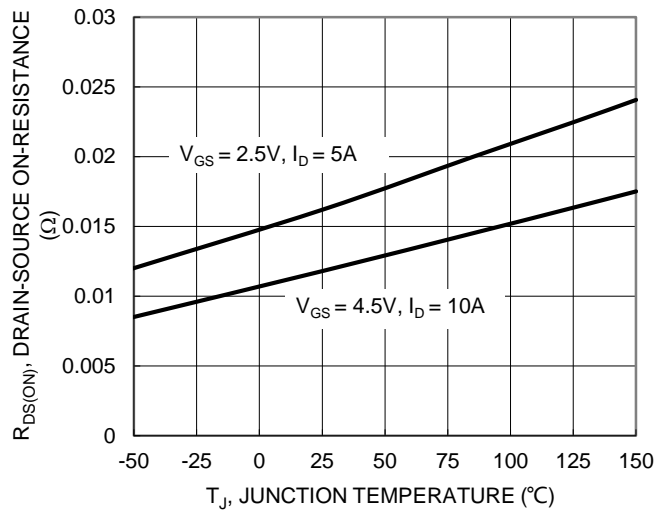


Figure 7. On-Resistance Variation with Junction Temperature

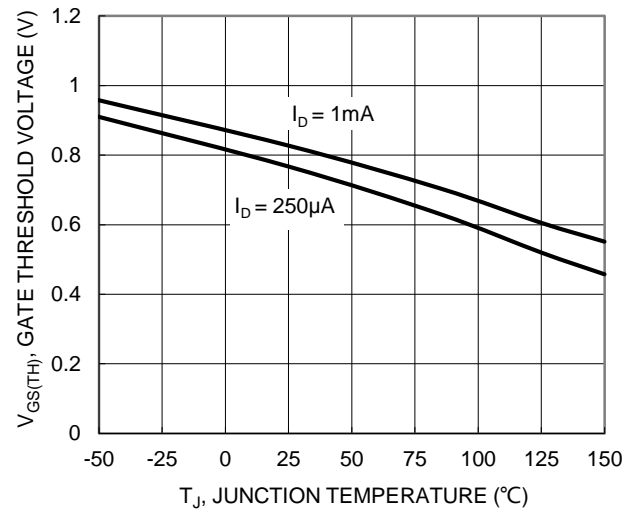


Figure 8. Gate Threshold Variation vs. Junction Temperature

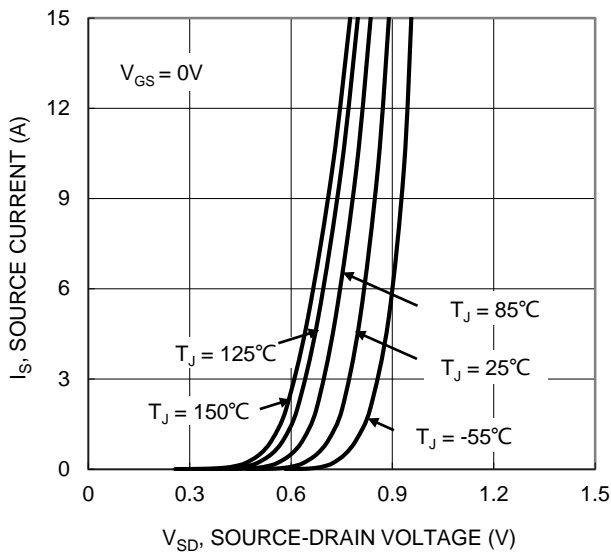


Figure 9. Diode Forward Voltage vs. Current

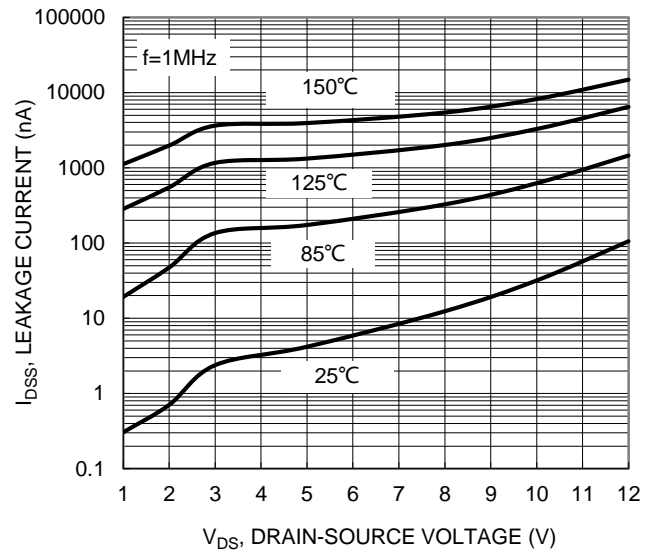


Figure 10. Typical Drain-Source Leakage Current vs Voltage

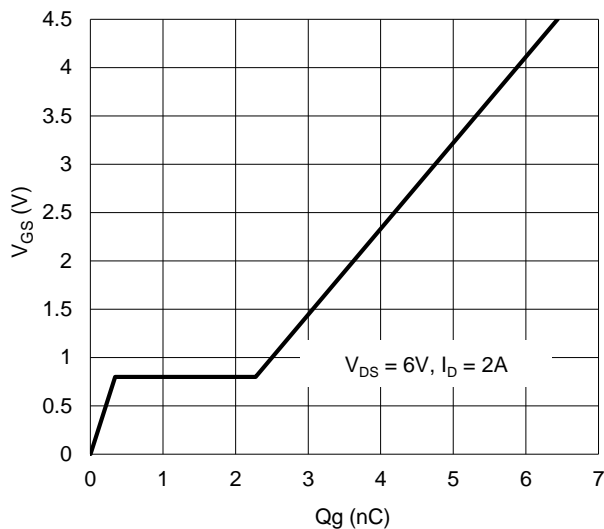


Figure 11. Gate Charge

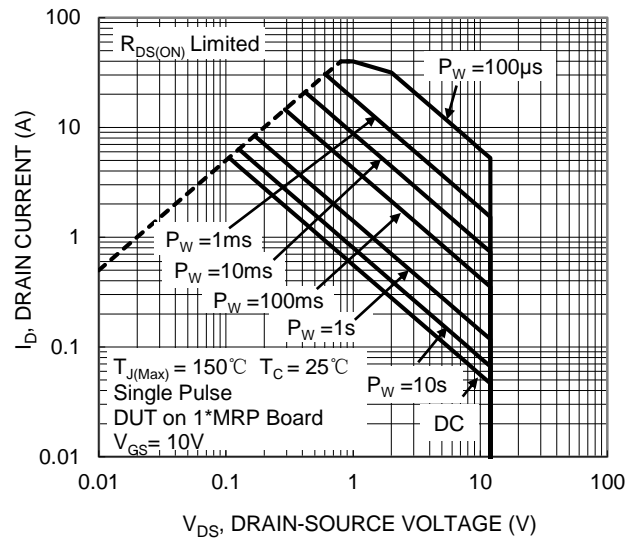


Figure 12. SOA, Safe Operation Area

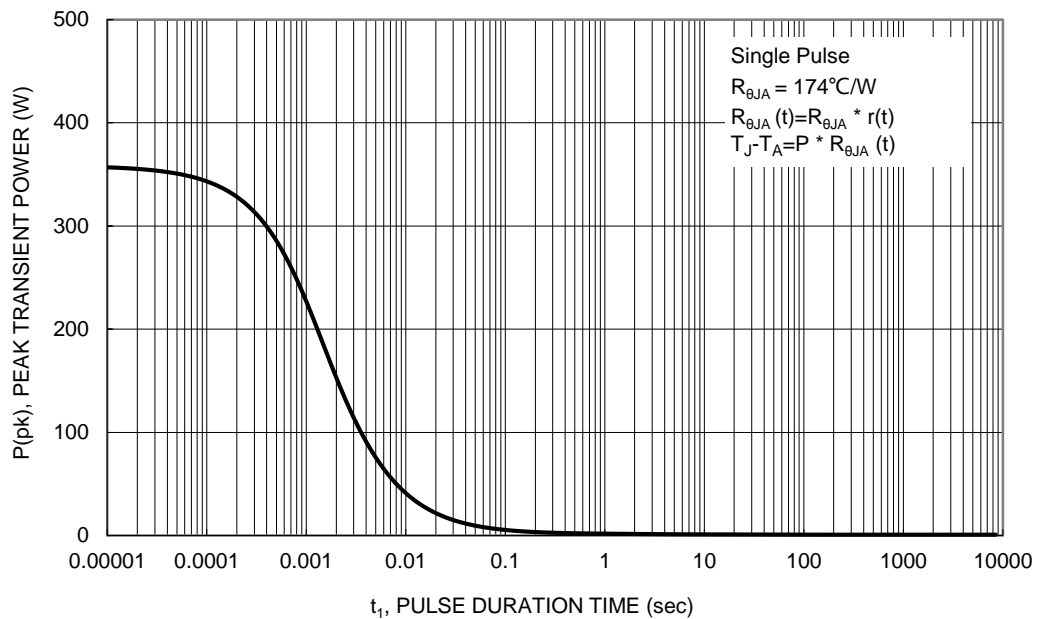


Figure 13. Single Pulse Maximum Power Dissipation

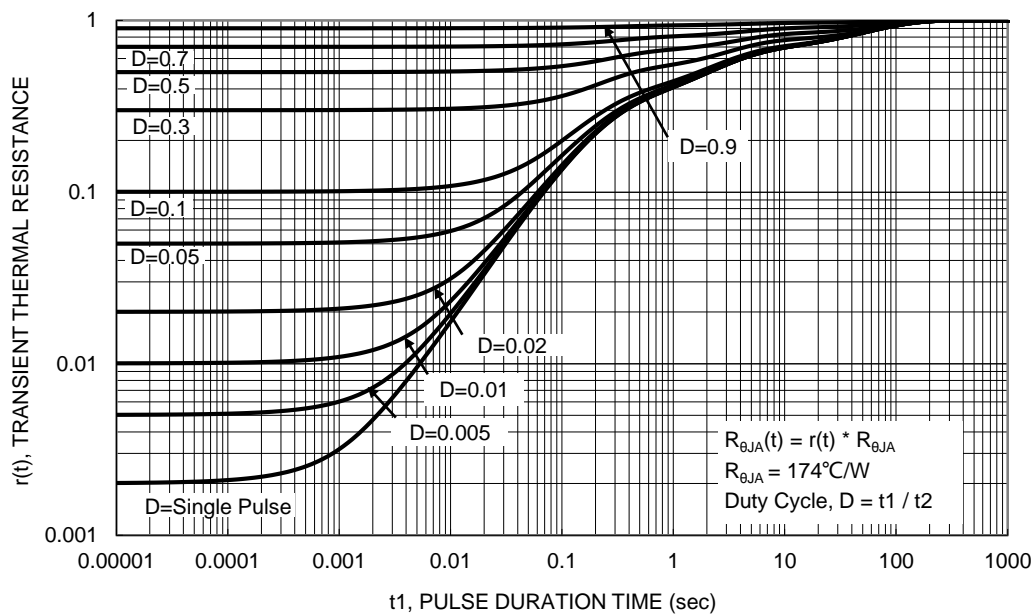
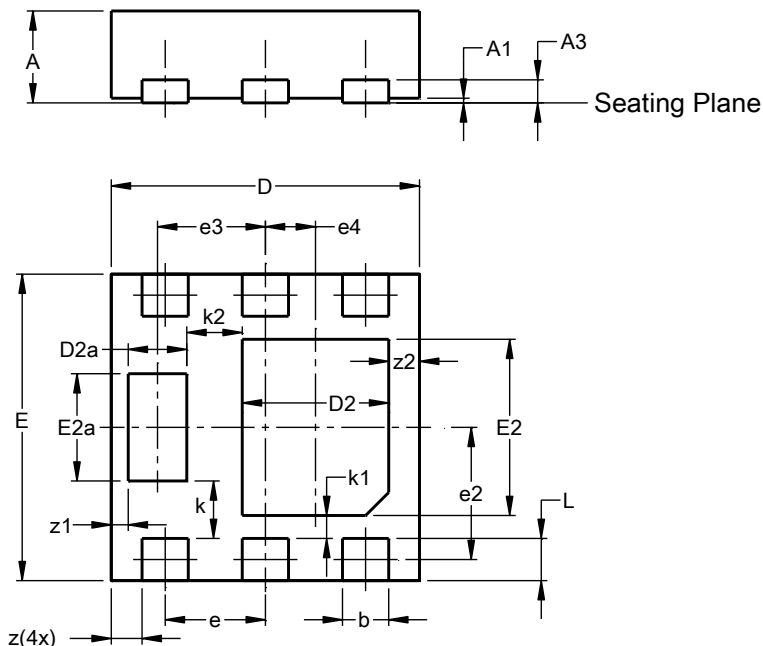


Figure 14. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)

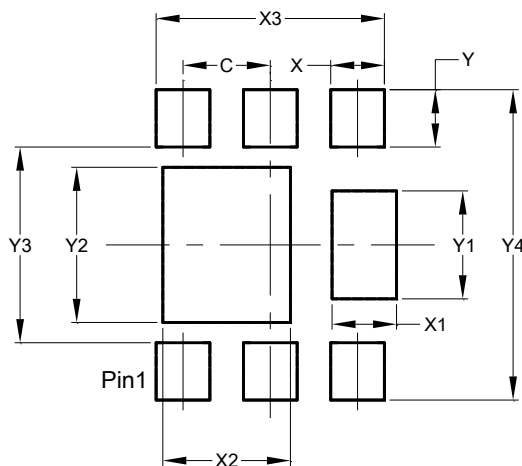


U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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